

ABSTRACT OF THE DISCLOSURE

The consumed power of a MOS type sensor including a floating diffusion (FD) amplifier in each pixel is reduced. For this purpose, drain regions (regions for supplying a pulse voltage to FD portions through reset transistors) of unit pixels are connected to different drain lines row by row, so as to selectively supply a power pulse to each row. The power pulse is set to a HIGH level potential at least during a period when signal charge stored in the FD portion is reset and a period when the signal charge stored in the FD portion is detected.